



BC857BW

SMALL SIGNAL PNP TRANSISTOR

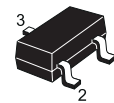
PRELIMINARY DATA

Type	Marking
BC857BW	3FW

- SILICON EPITAXIAL PLANAR PNP TRANSISTOR
- MINIATURE SOT-323 PLASTIC PACKAGE FOR SURFACE MOUNTING CIRCUITS
- TAPE AND REEL PACKING
- THE NPN COMPLEMENTARY TYPE IS BC847BW

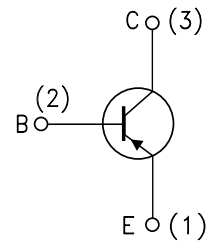
APPLICATIONS

- WELL SUITABLE FOR PORTABLE EQUIPMENT
- SMALL LOAD SWITCH TRANSISTOR WITH HIGH GAIN AND LOW SATURATION VOLTAGE



SOT-323

INTERNAL SCHEMATIC DIAGRAM



DS10120

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage ($I_E = 0$)	-50	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	-45	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	-5	V
I_C	Collector Current	-100	mA
I_{CM}	Collector Peak Current	-200	mA
P_{tot}	Total Dissipation at $T_C = 25\text{ }^\circ\text{C}$	200	mW
T_{stg}	Storage Temperature	-65 to 150	$^\circ\text{C}$
T_j	Max. Operating Junction Temperature	150	$^\circ\text{C}$

BC857BW

THERMAL DATA

R _{thj-amb} •	Thermal Resistance Junction-Ambient	Max	625	°C/W
------------------------	-------------------------------------	-----	-----	------

• Device mounted on a PCB area of 1 cm².

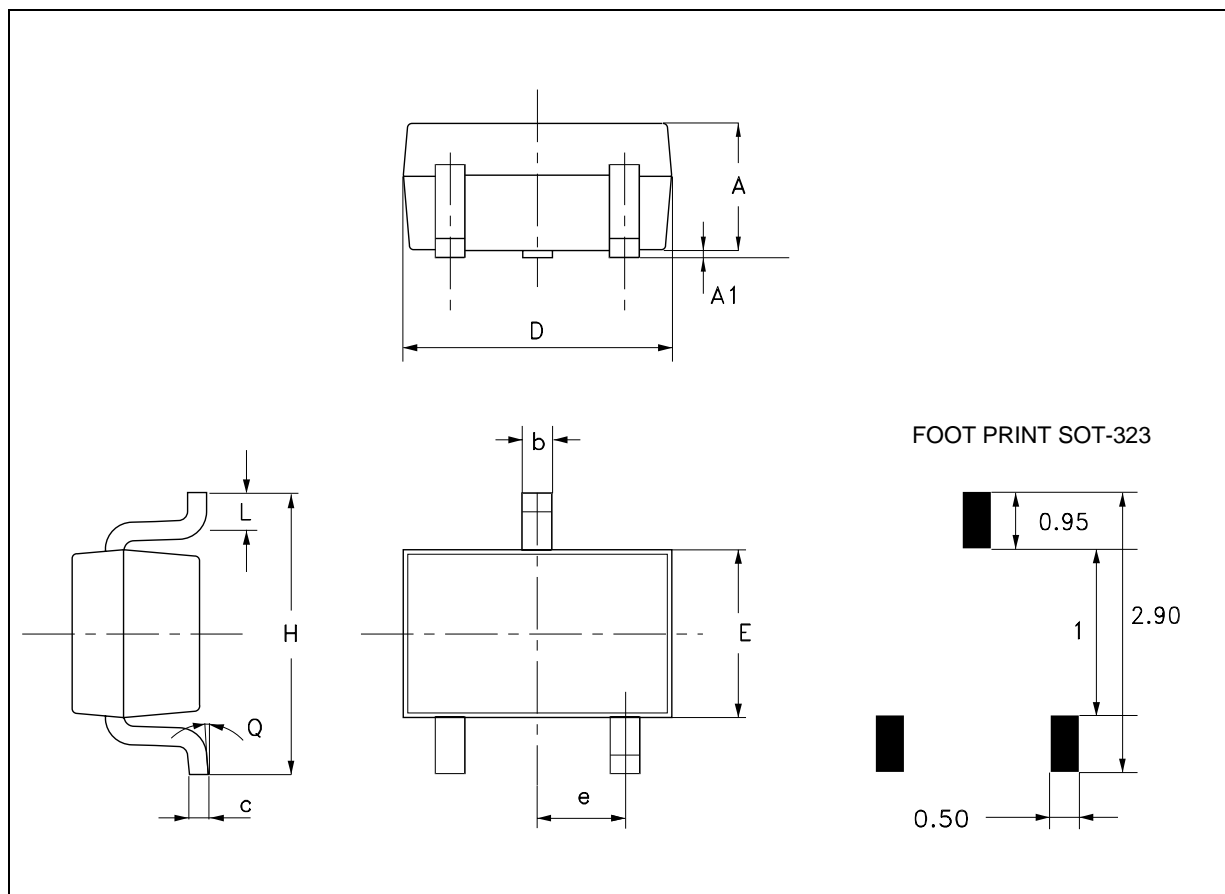
ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _{CBO}	Collector Cut-off Current (I _E = 0)	V _{CB} = -30 V V _{CB} = -30 V T _C = 150 °C		-1	-15 -5	nA μA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = -5 V			-100	nA
V _{(BR)CBO}	Collector-Base Breakdown Voltage (I _E = 0)	I _C = -10 μA	-50			V
V _{(BR)CEO*}	Collector-Emitter Breakdown Voltage (I _B = 0)	I _C = -2 mA	-45			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage (I _C = 0)	I _E = -10 μA	-5			V
V _{CE(sat)*}	Collector-Emitter Saturation Voltage	I _C = -10 mA I _B = -0.5 mA I _C = -100 mA I _B = -5 mA		-0.07 -0.25	-0.3 -0.65	V V
V _{BE(sat)*}	Base-Emitter Saturation Voltage	I _C = -10 mA I _B = -0.5 mA I _C = -100 mA I _B = -5 mA		-0.7 -0.85		V V
V _{BE(on)*}	Base-Emitter On Voltage	I _C = -2 mA V _{CE} = -5 V I _C = -10 mA V _{CE} = -5 V	-0.6	-0.65	-0.75 -0.82	V V
h _{FE*}	DC Current Gain	I _C = -2 mA V _{CE} = -5 V for BC857BW for BC857C	220 420		475 800	
f _T	Transition Frequency	I _C = -10 mA V _{CE} = -5 V f = 100MHz	100			MHz
C _{CBO}	Collector-Base Capacitance	I _E = 0 V _{CB} = -10 V f = 1 MHz		4.5		pF
NF	Noise Figure	V _{CE} = -5 V I _C = -0.2 mA f = 1KHz Δf = 200 Hz R _G = 2 KΩ		2	10	dB

* Pulsed: Pulse duration = 300 μs, duty cycle ≤ 2 %

SOT-323 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	0.8		1.1	0.031		0.043
A1	0		0.1	0		0.003
b	0.25		0.4	0.009		0.015
c	0.1		0.26	0.004		0.010
D	1.8	2.0	2.2	0.070	0.078	0.086
E	1.15	1.25	1.35	0.045	0.049	0.053
e		0.65			0.025	
H	1.8	2.1	2.4	0.070	0.082	0.094
L	0.1	0.2	0.3	0.004	0.007	0.011
Q	0		10°	0		10°



Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specification mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a trademark of STMicroelectronics

© 2002 STMicroelectronics – Printed in Italy – All Rights Reserved

STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - Canada - China - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States.

<http://www.st.com>

This datasheet has been download from:

www.datasheetcatalog.com

Datasheets for electronics components.